

MOSFET – Dual, N-Channel, Asymmetric, POWER TRENCH[®], Power Clip, 30 V

FDPC5018SG

General Description

This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET™ (Q2) have been designed to provide optimal power efficiency.

Features

- Q1: N-Channel
- Max $R_{DS(on)}$ = 5.0 mΩ at $V_{GS} = 10$ V, $I_D = 17$ A
 - Max $R_{DS(on)}$ = 6.5 mΩ at $V_{GS} = 4.5$ V, $I_D = 14$ A
- Q2: N-Channel
- Max $R_{DS(on)}$ = 1.6 mΩ at $V_{GS} = 10$ V, $I_D = 32$ A
 - Max $R_{DS(on)}$ = 2.0 mΩ at $V_{GS} = 4.5$ V, $I_D = 28$ A
 - Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses.
 - MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing.
 - ESD Protection Level: HBM > 500 V, CDM > 1 kV, MM > 100 V
 - RoHS Compliant

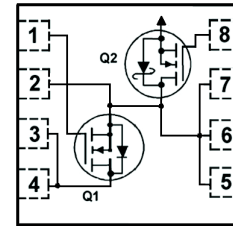
Applications

- Computing
- Communications
- General Purpose Point of Load

Table 1. PIN DESCRIPTION

Pin	Name	Description
1	HSG	High Side Gate
2	GR	Gate Return
3, 4, 9	V+(HSD)	High Side Drain
5, 6, 7	SW	Switching Node, Low Side Drain
8	LSG	Low Side Gate
10	GND (LSS)	Low Side Source

ELECTRICAL CONNECTION



N-Channel MOSFET

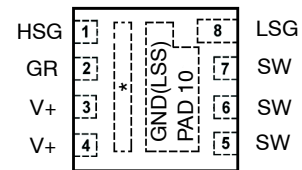


Top View

Bottom View

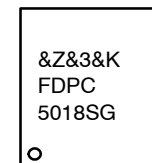
Power Clip 56
(PQFN8 5x6)
CASE 483AR

PIN ASSIGNMENT



*PAD 9 V+(HSD)

MARKING DIAGRAM



- &Z = Assembly Plant Code
- &3 = Date Code (Year & Week)
- &K = Lot Traceability Code
- FDPC5018SG = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

FDPC5018SG

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, Unless otherwise noted.)

Symbol	Parameter	Q1	Q2	Unit
V_{DS}	Drain to Source Voltage	30	30	V
$Bvdsst$	$Bvdsst$ (Transient) < 100 ns	32.5	32.5	V
V_{GS}	Gate to Source Voltage	± 20	± 12	V
I_D	Drain Current – Continuous ($T_C = 25^\circ\text{C}$) (Note 5)	56	109	A
	– Continuous ($T_C = 100^\circ\text{C}$) (Note 5)	35	69	
	– Continuous ($T_A = 25^\circ\text{C}$)	17 (Note 1a)	32 (Note 1b)	
	– Pulsed ($T_A = 25^\circ\text{C}$) (Note 4)	227	704	
E_{AS}	Single Pulsed Avalanche Energy (Note 3)	54	181	mJ
P_D	Power Dissipation for Single Operation ($T_C = 25^\circ\text{C}$) ($T_A = 25^\circ\text{C}$) ($T_A = 25^\circ\text{C}$)	23 2.1 (Note 1a) 1.0 (Note 1c)	29 2.3 (Note 1b) 1.1 (Note 1d)	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150		$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.6	4.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60 (Note 1a)	55 (Note 1b)	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	130 (Note 1c)	120 (Note 1d)	$^\circ\text{C}/\text{W}$

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
--------	-----------	-----------------	------	-----	-----	-----	-------

OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$ $I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	Q1 Q2	30 30	– –	– –	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C $I_D = 10 \text{ mA}$, referenced to 25°C	Q1 Q2	– –	15 19	– –	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	Q1 Q2	– –	– –	1 500	μA μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$	Q1 Q2	– –	– –	100 100	nA nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$ $V_{GS} = V_{DS}, I_D = 1 \text{ mA}$	Q1 Q2	1.0 1.0	1.7 1.6	3.0 3.0	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C $I_D = 10 \text{ mA}$, referenced to 25°C	Q1 Q2	– –	–5 –3	– –	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 14 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}, T_J = 125^\circ\text{C}$	Q1	– –	4.1 5.4 5.7	5.0 6.5 7.0	m Ω
		$V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 28 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}, T_J = 125^\circ\text{C}$	Q2	– –	1.4 1.7 2.1	1.6 2.0 2.4	
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 17 \text{ A}$ $V_{DS} = 5 \text{ V}, I_D = 32 \text{ A}$	Q1	–	93	–	S
			Q2	–	188	–	

FDPC5018SG

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted.) (continued)

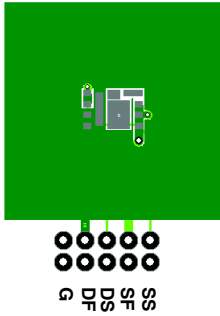
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units	
DYNAMIC CHARACTERISTICS								
C_{iss}	Input Capacitance	Q1: $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ Q2: $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Q1	–	1224	1715	pF	
			Q2	–	4593	6430		
C_{oss}	Output Capacitance		Q1	–	397	560	pF	
			Q2	–	1210	1695		
C_{rss}	Reverse Transfer Capacitance		Q1	–	42	60	pF	
			Q2	–	80	115		
R_g	Gate Resistance		Q1	0.1	0.5	1.5	Ω	
			Q2	0.1	0.8	2.4		
SWITCHING CHARACTERISTICS								
$t_{d(on)}$	Turn-On Delay Time	Q1: $V_{DD} = 15\text{ V}, I_D = 17\text{ A}, R_{GEN} = 6\ \Omega$ Q2: $V_{DD} = 15\text{ V}, I_D = 32\text{ A}, R_{GEN} = 6\ \Omega$	Q1	–	8	16	ns	
			Q2	–	14	25		
t_r	Rise Time			Q1	–	2	10	ns
				Q2	–	5	10	
$t_{d(off)}$	Turn-Off Delay Time		Q1	–	18	33	ns	
			Q2	–	38	61		
t_f	Fall Time		Q1	–	2	10	ns	
			Q2	–	4	10		
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	Q1 $V_{DD} = 15\text{ V},$ $I_D = 17\text{ A}$ Q2 $V_{DD} = 15\text{ V},$ $I_D = 32\text{ A}$	Q1	–	17	24	nC
				Q2	–	62	87	
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$		Q1	–	8	11	nC
				Q2	–	28	40	
Q_{gs}	Gate to Source Gate Charge		Q1	–	3.1	–	nC	
			Q2	–	11	–		
Q_{gd}	Gate to Drain "Miller" Charge		Q1	–	2.0	–	nC	
			Q2	–	5.3	–		
DRAIN-SOURCE DIODE CHARACTERISTICS								
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 17\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = 32\text{ A}$ (Note 2)	Q1	–	0.8	1.2	V	
			Q2	–	0.8	1.2		
t_{rr}	Reverse Recovery Time	Q1 $I_F = 17\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1	–	23	37	ns	
			Q2	–	32	51		
Q_{rr}	Reverse Recovery Charge	Q2 $I_F = 32\text{ A}, di/dt = 240\text{ A}/\mu\text{s}$	Q1	–	8	16	nC	
			Q2	–	40	64		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

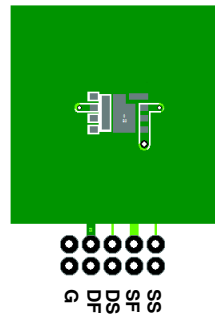
FDPC5018SG

NOTES:

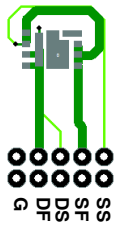
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



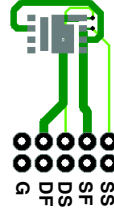
a) 60°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 55°C/W when mounted on a 1 in² pad of 2 oz copper.



c) 130°C/W when mounted on a minimum pad of 2 oz copper.



d) 120°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Q1: E_{AS} of 54 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 3\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 30\text{ V}$. $V_{GS} = 10\text{ V}$, 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 20\text{ A}$.
- Q2: E_{AS} of 181 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 3\text{ mH}$, $I_{AS} = 11\text{ A}$, $V_{DD} = 30\text{ V}$. $V_{GS} = 10\text{ V}$, 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 36\text{ A}$.
4. Pulsed Id refer to Figure 11 and Figure 24 SOA graphs for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

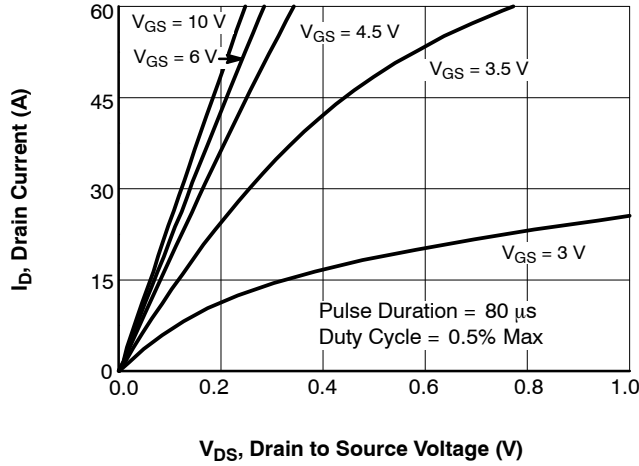


Figure 1. On-Region Characteristics

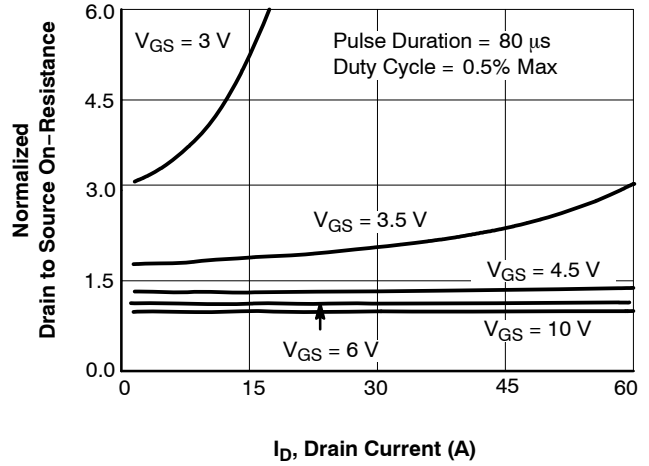


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

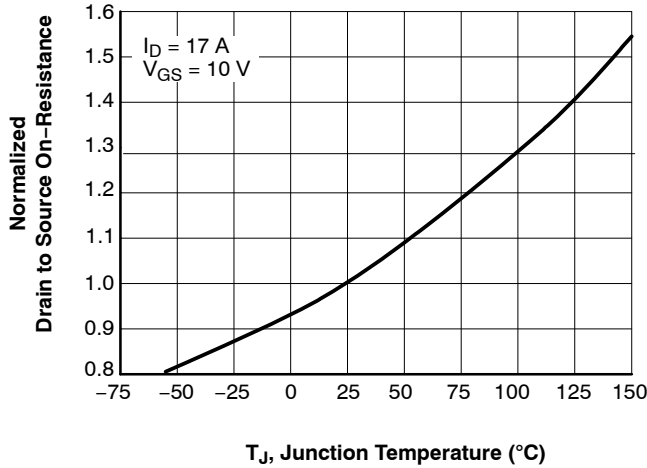


Figure 3. Normalized On-Resistance vs. Junction Temperature

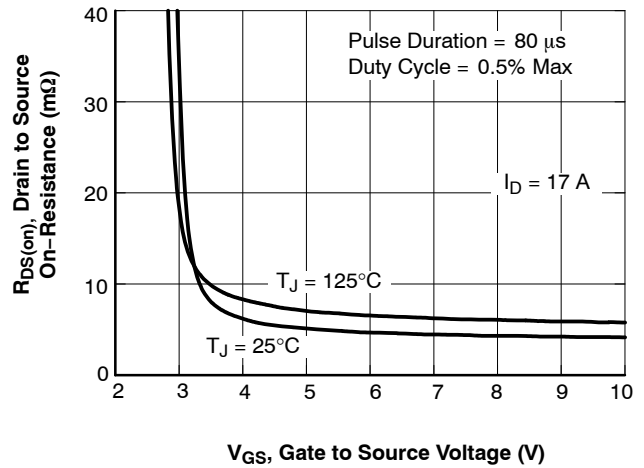


Figure 4. On-Resistance vs. Gate to Source Voltage

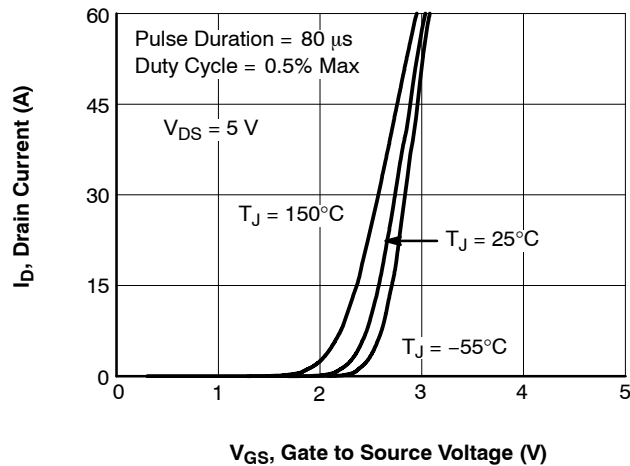


Figure 5. Transfer Characteristics

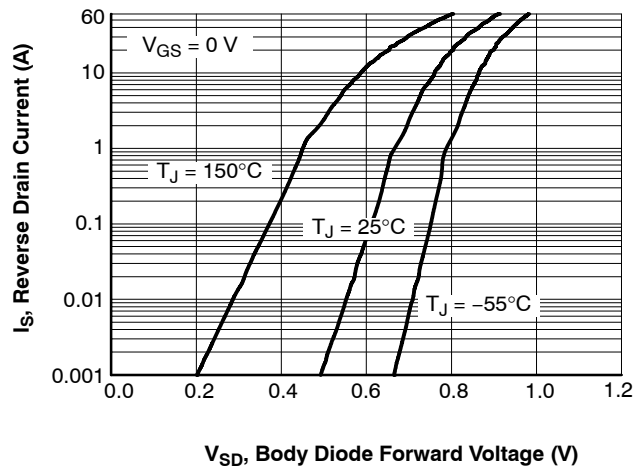


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

FDPC5018SG

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

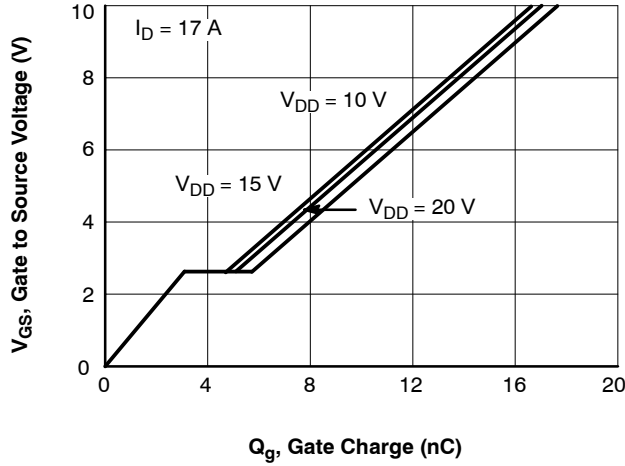


Figure 7. Gate Charge Characteristics

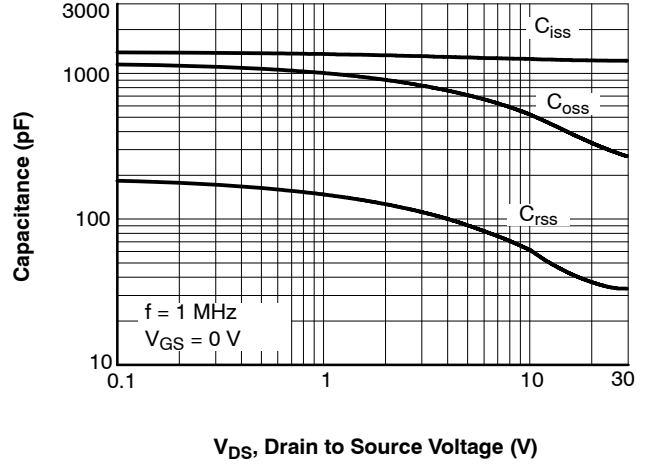


Figure 8. Capacitance vs. Drain to Source Voltage

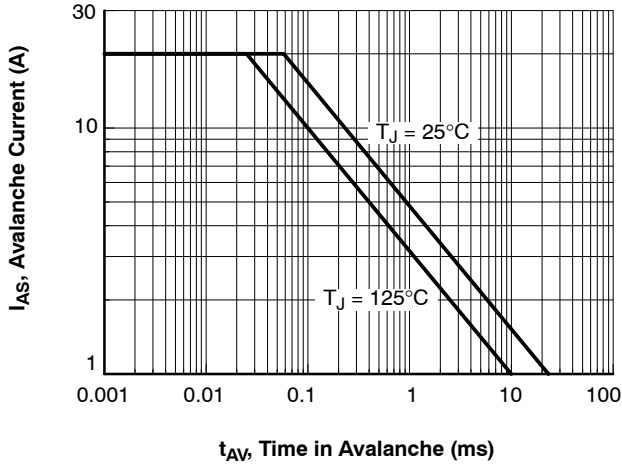


Figure 9. Unclamped Inductive Switching Capability

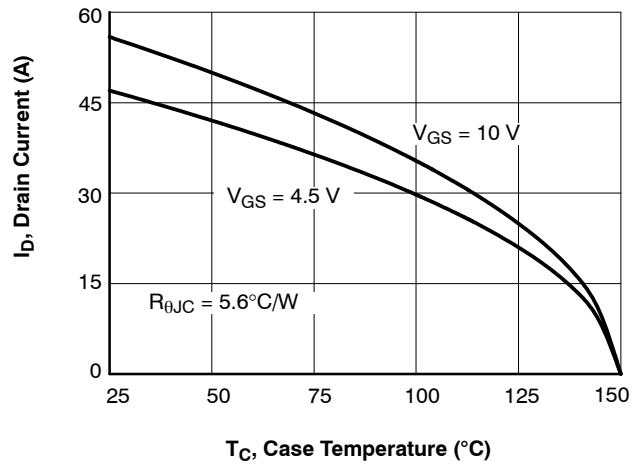


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

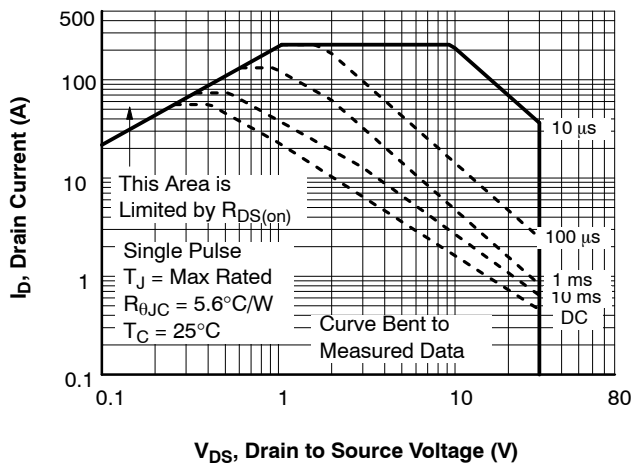


Figure 11. Forward Bias Safe Operating Area

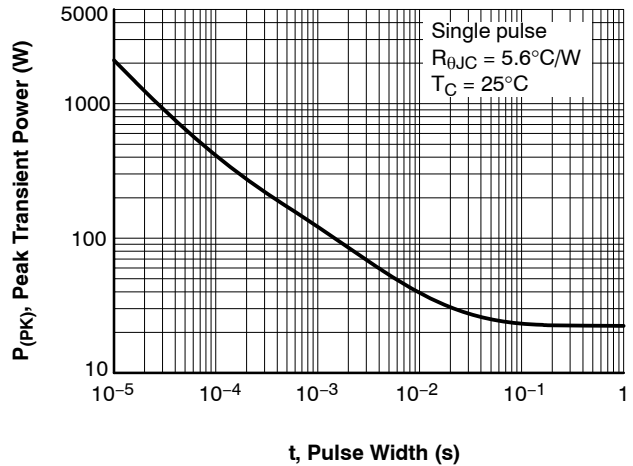


Figure 12. Single Pulse Maximum Power Dissipation

FDPC5018SG

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

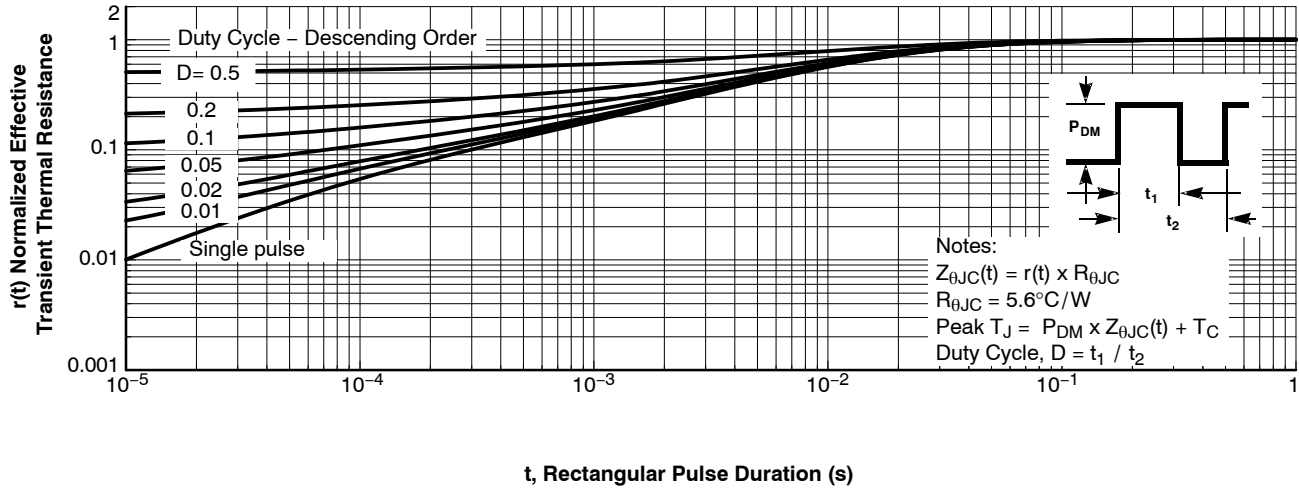


Figure 13. Junction-to-Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

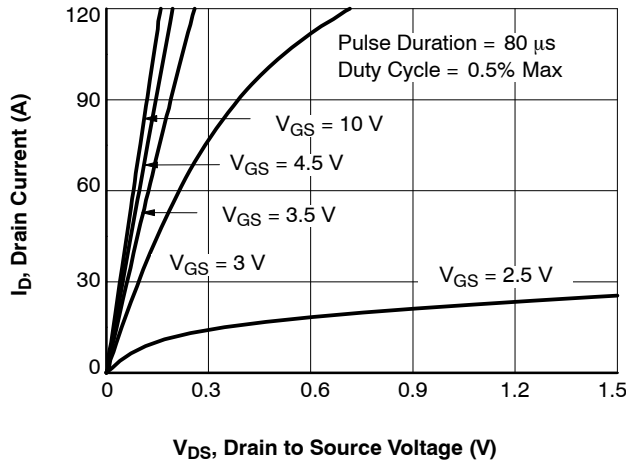


Figure 14. On-Region Characteristics

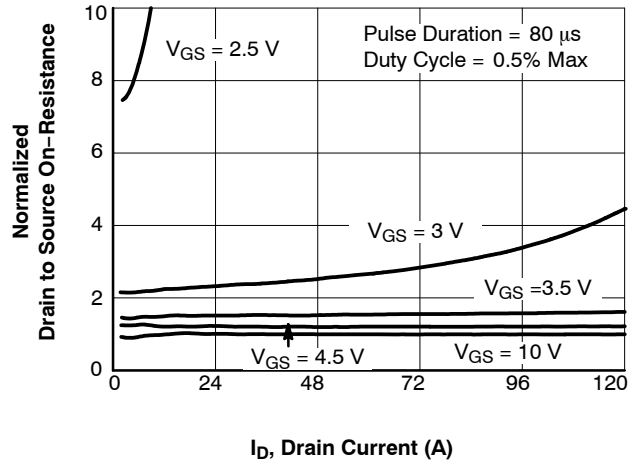


Figure 15. Normalized On-Resistance vs. Drain Current and Gate Voltage

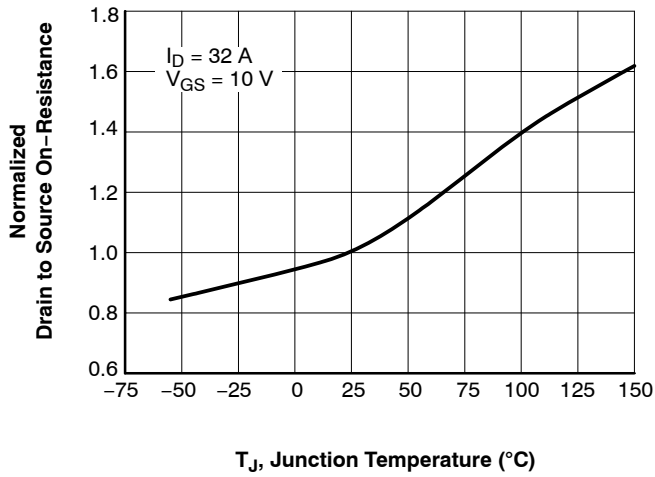


Figure 16. Normalized On-Resistance vs. Junction Temperature

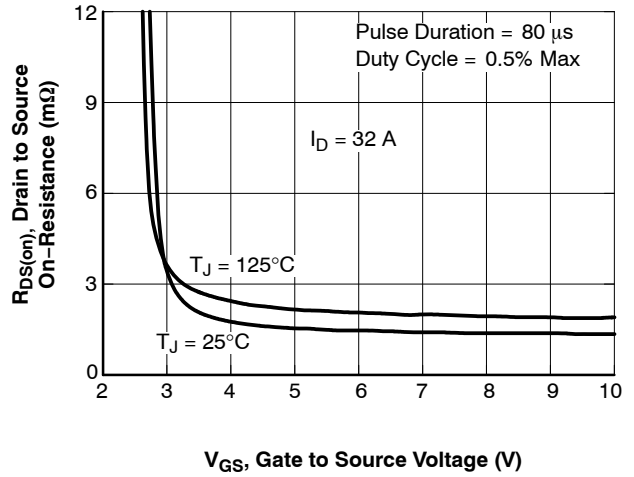


Figure 17. On-Resistance vs. Gate to Source Voltage

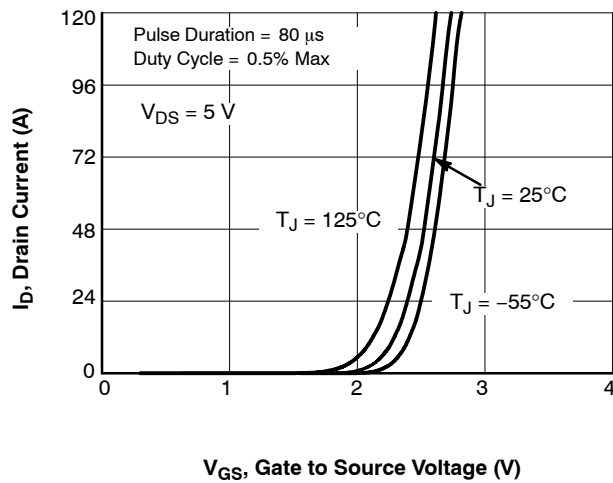


Figure 18. Transfer Characteristics

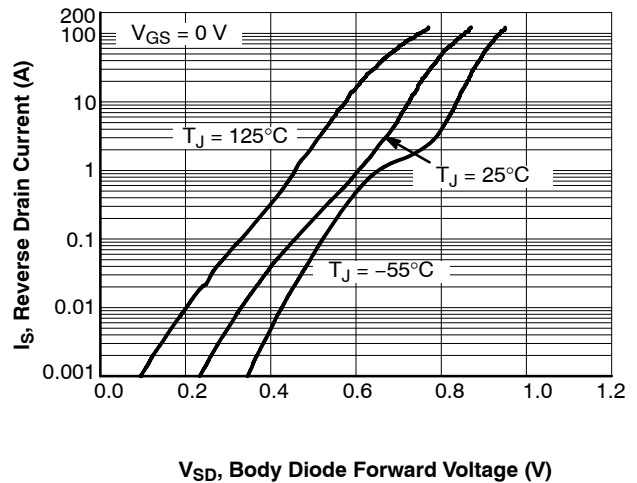


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

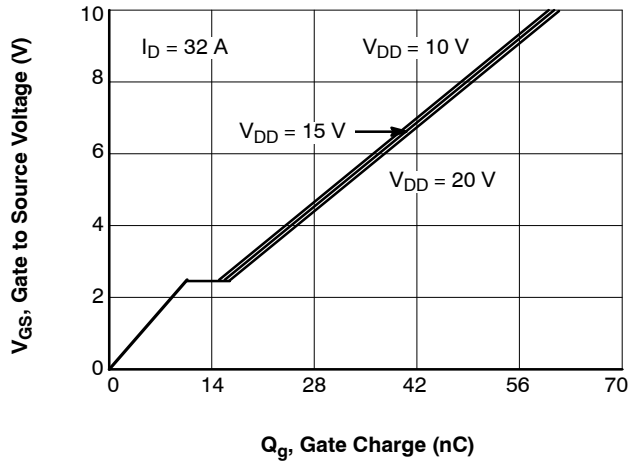


Figure 20. Gate Charge Characteristics

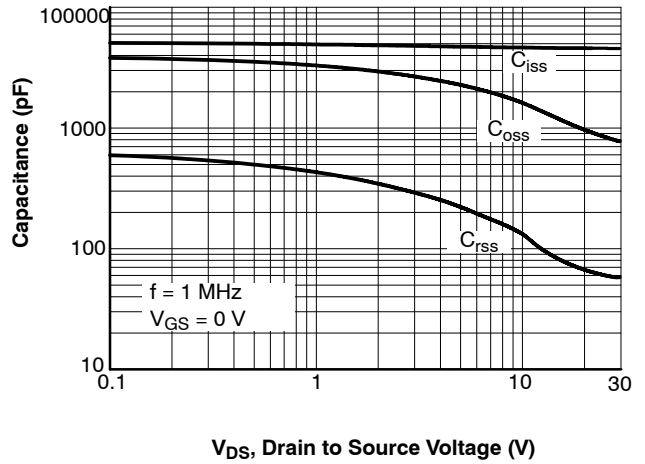


Figure 21. Capacitance vs. Drain to Source Voltage

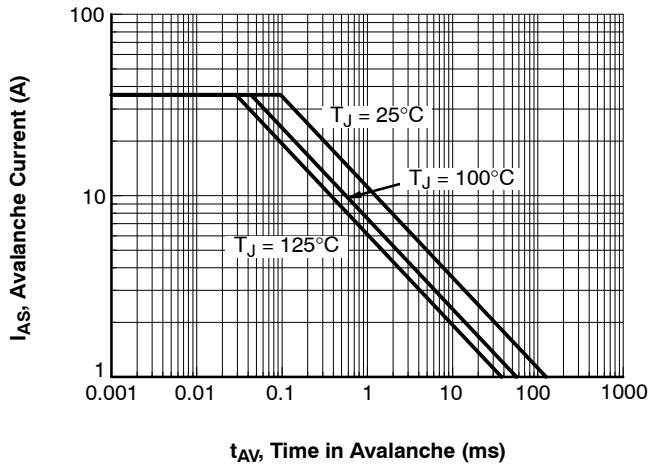


Figure 22. Unclamped Inductive Switching Capability

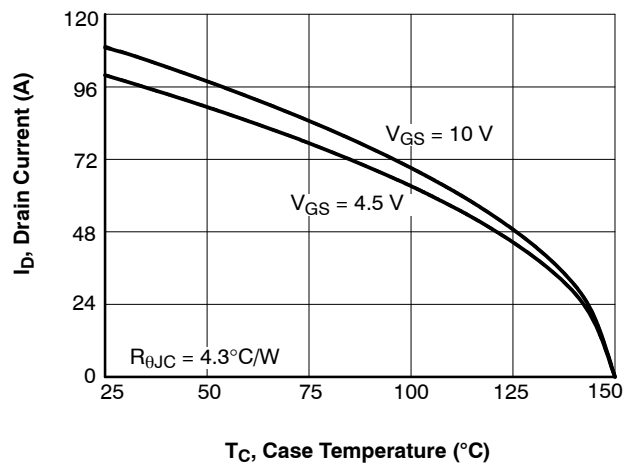


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

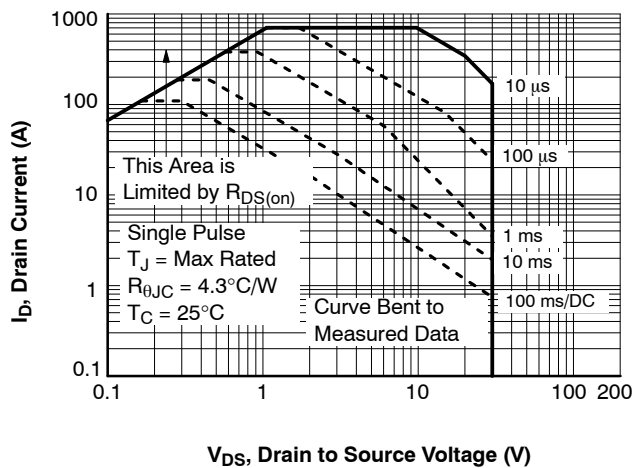


Figure 24. Forward Bias Safe Operating Area

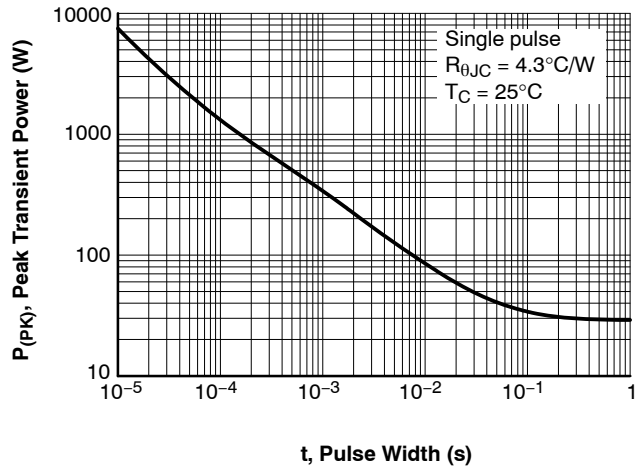


Figure 25. Single Pulse Maximum Power Dissipation

FDPC5018SG

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

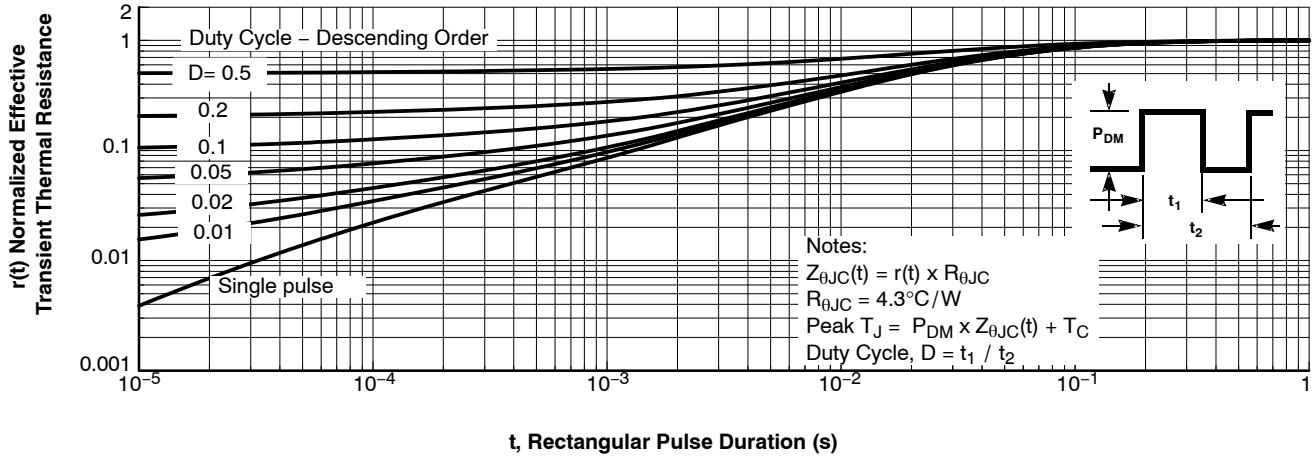


Figure 26. Junction-to-Case Transient Thermal Response Curve

FDPC5018SG

TYPICAL CHARACTERISTICS (continued)

SyncFET Schottky Body Diode Characteristics

onsemi's SyncFET process embeds a Schottky diode in parallel with POWERTRENCH MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverse recovery characteristic of the FDPC5018SG.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

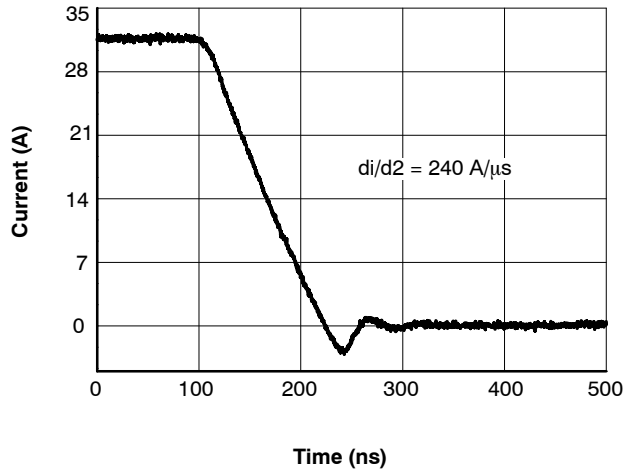


Figure 27. SyncFET Body Diode Reverse Recovery Characteristic

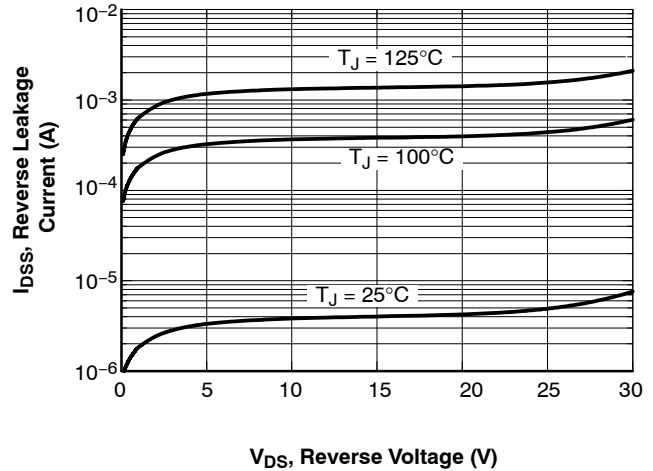


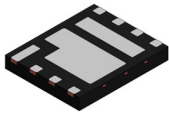
Figure 28. SyncFET Body Diode Reverse Leakage vs. Drain-Source Voltage

PACKAGE MARKING AND ORDERING INFORMATION

Device	Top Marking	Package	Reel Size	Tape Width	Shipping†
FDPC5018SG	FDPC5018SG	Power Clip 56	13"	12 mm	3,000 / Tape & Reel

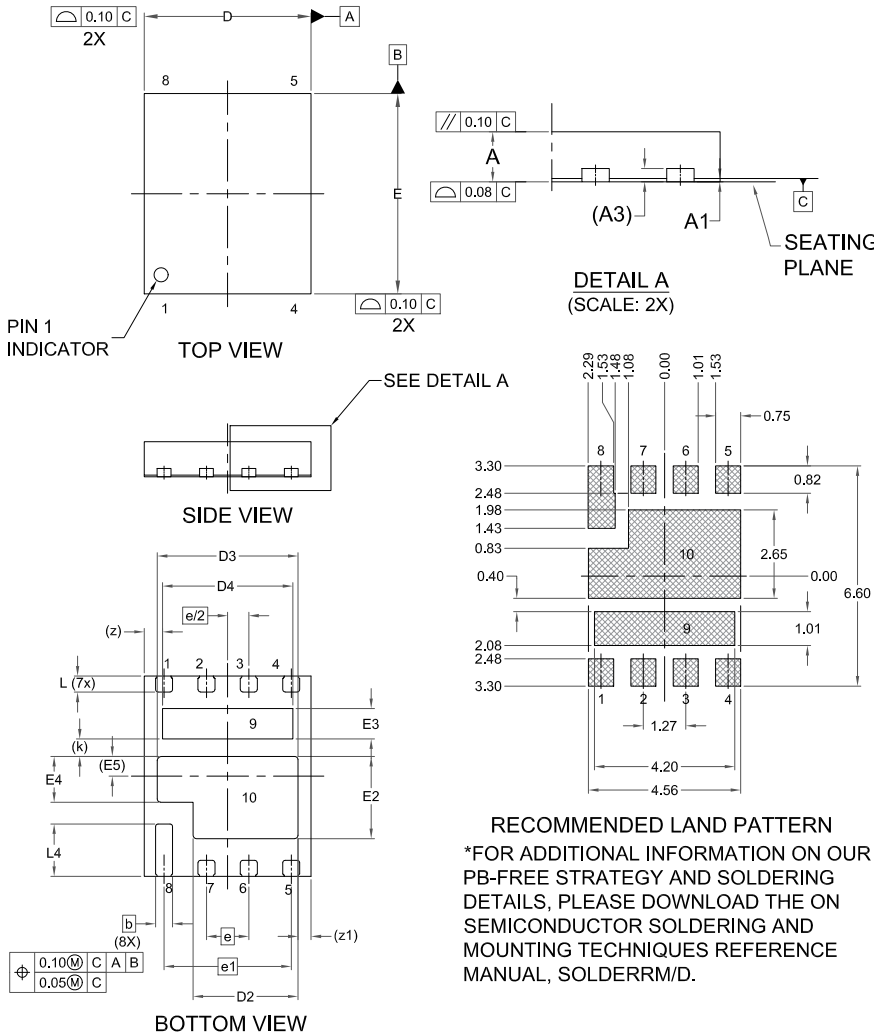
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

POWERTRENCH is registered trademark and SyncFET is a trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries



PQFN8 5.00x6.00x0.75, 1.27P
CASE 483AR
ISSUE D

DATE 06 NOV 2023



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.51 BSC		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
D3	4.12	4.22	4.32
D4	3.80	3.90	4.00
E	5.90	6.00	6.10
E2	2.36	2.46	2.56
E3	0.81	0.91	1.01
E4	1.27	1.37	1.47
E5	0.59 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
k	0.52 REF		
L	0.38	0.48	0.58
L4	1.47	1.57	1.67
z	0.55 REF		
z1	0.39 REF		

RECOMMENDED LAND PATTERN
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

DOCUMENT NUMBER:	98AON13666G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	PQFN8 5.00x6.00x0.75, 1.27P	PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales